Preferred Device

PNP Silicon Transistor

Features

• Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-300	Vdc
Collector-Base Voltage	V _{CBO}	-300	Vdc
Collector-Emitter Voltage	V _{CER}	-300	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current	IC	-50	mAdc
Total Power Dissipation up to T _A = 25°C (Note 1)	P _D	1.5	W
Storage Temperature Range	T _{stg}	- 65 to +150	°C
Junction Temperature	TJ	150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	83.3	°C/W	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

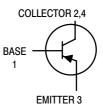
Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 in².



ON Semiconductor®

http://onsemi.com

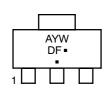
PNP SILICON TRANSISTOR SURFACE MOUNT







SOT-223 (TO-261) CASE 318E STYLE 1



A = Assembly Location

= Year

W = Work Week
DF = Device Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BF721T1	SOT-223	1000 / Tape & Reel
BF721T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	-	•	•	
Collector-Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _{(BR)CEO}	-300	-	Vdc
Collector-Base Breakdown Voltage ($I_C = -100 \mu Adc, I_E = 0$)	V _(BR) CBO	-300	-	Vdc
Collector-Emitter Breakdown Voltage (I_C = -100 μ Adc, R_{BE} = 2.7 $k\Omega$)	V _(BR) CER	-300	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-5.0	-	Vdc
Collector-Base Cutoff Current $(V_{CB} = -200 \text{ Vdc}, I_E = 0)$	I _{CBO}	-	-10	nAdc
Collector-Emitter Cutoff Current (V _{CE} = -250 Vdc, R _{BE} = 2.7 k Ω) (V _{CE} = -200 Vdc, R _{BE} = 2.7 k Ω , T _J = 150°C)	ICER	- -	-50 -10	nAdc μAdc
ON CHARACTERISTICS	<u>.</u>		•	
DC Current Gain (I _C = -25 mAdc, V _{CE} = -20 Vdc)	h _{FE}	50	-	-
Collector-Emitter Saturation Voltage ($I_C = -30 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	-	-0.8	Vdc
DYNAMIC CHARACTERISTICS	-	•		•
Current-Gain - Bandwidth Product ($V_{CE} = -10 \text{ Vdc}, I_{C} = -10 \text{ mAdc}, f = 35 \text{ MHz}$)	f _T	60	-	MHz
Feedback Capacitance (V _{CE} = -30 Vdc, I _C = 0, f = 1.0 MHz)	C _{re}	-	1.6	pF

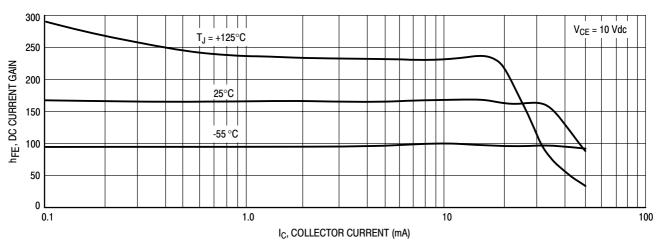


Figure 1. DC Current Gain

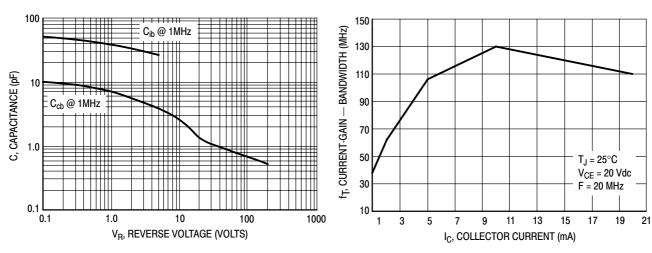
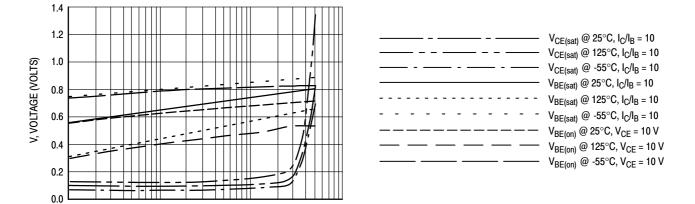


Figure 2. Capacitance



100

Figure 3. Current-Gain — Bandwidth

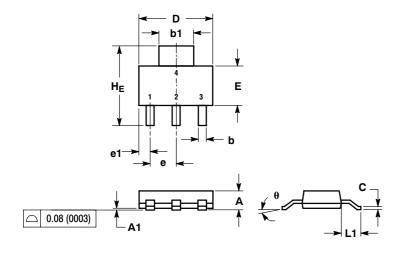
I_C, COLLECTOR CURRENT (mA)

Figure 4. "ON" Voltages

0.1

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 **ISSUE L**



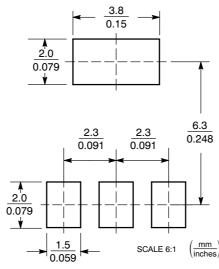
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
 - Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

- PIN 1. BASE COLLECTOR
 - 3. **EMITTER**
 - COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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